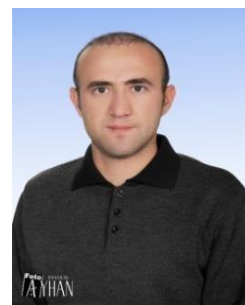


# AHMAD ASIMOV

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## WORK EXPERIENCE

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- **Researcher**, Organic laboratory of Gabza High Technical University's
- **Researcher**, Center of ODTU University
- **Researcher**, Research and Development Center for High Technologies, Ministry of Communications and High Technologies, Azerbaijan.
- **Researcher**, Azerbaijan National Academy of Sciences of Physics Institute in laboratory of «Thin film structures»
- ✓ **Azerbaijan National Academy of Sciences, Institute of Physics, “Thin film structures” laboratory. Leading Researcher. Baku, Azerbaijan, 2016 –2023 .**
- ✓ **Khazar University. Lecturer and researcher (part time). Baku, Azerbaijan, From 2020 – present**
- ✓ **Department of Engineering and Applied Sciences, UNEC Lecturer and researcher Baku, Azerbaijan, From 2023 – present**
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## EDUCATION

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- 2003-2007            **BSc in Physics**, Baku State University, Azerbaijan, Baku
- 2008-2010        **MSc in Physics**, Gazi University, Turkey, Ankara
- 2010-2014        **Ph.D. in Physics**, Uludag University, Turkey, Bursa

## LANGUAGES

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- Azerbaijan (native)
- English (fluent)
- Turkish (fluent)

## QUALIFICATIONS

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- Office Programs, Windows 2000/XP, Microsoft Office 97/2000,2003/2007
- Matlab, Origin 8.1

# RESEARCH INTEREST

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- Metal Organic Vapor Phase Epitaxy (MOVPE), SEM, AFM, Solar simulator
- Semiconductor technology:
  - Crystal growth: Metal Organic Vapor Phase Epitaxy (MOVPE).
  - Device Processing: Spin coating, organic-nanomaterial composites coating
- Characterization tools:
  - Atomic Force Microscopy (AFM)
  - Scanning Electron Microscopy SEM)
  - Photoluminescence (PL)
  - Electroluminescence (EL)
  - X-Ray Diffraction (XRD)

# PUBLICATIONS

1. B. Emdadi A. Asimov Synthesis and investigation of structural and optical properties of nitrogen doped Carbon Quantum Dot INTEGRATED FERROELECTRICS Vol 240 (1) 2024
2. R.Abaszade F. Tatardar R. Moradi M. Jafarov A. Mammadov A. Asimov R.d Safarov Graphene Oxide-Polyvinyl Alcohol Nanofibrous Composites: Fabrication, Properties, and Analysis accepted 2024
3. B. Emdadi A. Asimov Structural and Optical properties of PEDOT: PSS has been favorably reviewed and accepted for publication in INTEGRATED FERROELECTRICS Vol 237. 2023
4. M. Mammadzada, A. Asimov. Management With Fuzzy Logic Of Electrical Energy Obtained From Solar Panels And Application In Intelligent Home Systems. Proceedings Of Azerbaijan High Technical Educational Institutions (Pahtei) Volume 32, №09, Issn 2674-5224, 2023
5. M. Mammadzada, A. Asimov, Energy Management In The Smart Home Khazar Journal Of Science And Technology Vol. 6, №285-89, Issn 2520-6133, 2022
6. Kirsoy, M. Ahmetoglu (Afrailov), A. Asimov, B. Kucur A The Electrical Properties of Au/P3HT/n-GaAs Schottky Barrier Diode Acta Physica Polonica A Vol. 128 (2015) No. 2-B.

7. M. Ahmetoglu (Afrailov), A. Kirsoy, A. Asimov, B. Kucur. The Electrical Properties Of Au/Meh-ppv:pcbm/n-Type GaAs Schottky Barrier Diode. Optoelectronics And Advanced Materials Rapid Comunication vol 10, No.11-12,Nov-Dec.2016, P 825-830
8. A. Asimov, M. Ahmetoglu, A. Kirsoy, M. Özer, M. Yasin. The electrical properties of Au/P3HT/n-TYPE Si diode. Journal of Nanoelectronics and Optoelectronics Vol. 10 pp. 1–5, (2015)
9. A. Asimov, M. Ahmetoglu. The calculation of electronic parameters of Al/MDMO-PPV/p-Si/Al Schottky diode by current–voltage characteristics. Optoelectronics and Advanced Materials. (2014).
8. A. Asimov, M.Ahmetoglu, B.Kucur, İ Gucuyener Electrical characteristics of Al/n-type GaAs Schottky barrier diodes at room temperature Optoelectronics and Advanced Materials–Rapid Communications vol 18 2014
9. A. Asimov, M.Ahmetoglu, B.Kucur, M.Özer, T.Güzel. The determination of series resistance and interface state density distributions of Au/p-type GaAs Schottky barrier diodes. Optoelectronics And Advanced Materials . (2013 ) Vol. 7, No. 7-8.
10. M.Özer, T. Güzel, A. Asimov, M. Ahmetoglu. Gaussian Distribution of Inhomogeneous Barrier Height in Au/n-GaP (100) Schottky Barrier Diodes. Optoelectronics And Advanced Materials–Rapid Communications. (2013)
11. A. Asimov, K.Akay. Temperature Dependence of Barrier Heights of Au/p-GaAs Schottky Structures. FIZIKA vol. XVII №4, section: En. (2012)
12. M. Sel, A. Asimov, E. Huseynov.The Analysis of series resistance and interface state density distributions of Au/TiO<sub>2</sub>/n-Si Metal-Insulator-Semiconductor structures at room temperature.Transactions of Azerbaijan National Academy of Sciences N2pp.31-36. (2013)
13. M. Sel, A. Asimov, E. Huseynov. The temperature dependent electrical characteristics of Au/TiO<sub>2</sub>/n-Si Metal-Insulator-Semiconductor structures using C–V and G/w–V measurements. Transactions of Azerbaijan National Academy of Sciences. (2013)
14. A. Asimov, E. Huseynov. GaAs Tabanı Üzerinde Oluşturulan Schottky Diodların Temel Elektriksel Parametrelerinin Kapasitans-Voltaj (C-V) Ölçümlerinden Hesaplanması Qafqaz Üniversitesi Fizika Jurnalı (2013).
14. Babak EMDADI, Ahmet ASIMOV Insights and Difficulties in the Synthesis of Carbon Quantum Dots From Recyclable Materials Davamlı inkişaf strategiyası: qlobal trendlər, milli təcrübələr və yeni hədəflər” mövzusunda II BEYNƏLXALQ ELMİ KONFRANS, 2023

15. B. EMDADI, A. ASIMOV Synthesis and Investigation of Structural and Optical Nitrogen-Doped Carbon Quantum III. Interdisciplinary Conference on Mechanics, Computers and Electrics ICMECE 2023
  16. Babak Emdadi, Ahmed Asimov. Structural and Optical Properties of PEDOT: PSS. *Integrated Ferroelectrics*, Volume 237, 2023, p. 125-132
  17. Babak Emdadi, Ahmed Asimov. Synthesis and Investigation of Structural and Optical Properties of Nitrogen-doped Carbon Quantum Dots. *Integrated Ferroelectrics*, Volume 240, 2024, p. 175-180
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